# **DMC20402**

## Silicon NPN epitaxial planar type

For general amplification

#### ■ Features

• High forward current transfer ratio h<sub>FE</sub> with excellent linearity

Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: B6

#### ■ Basic Part Number

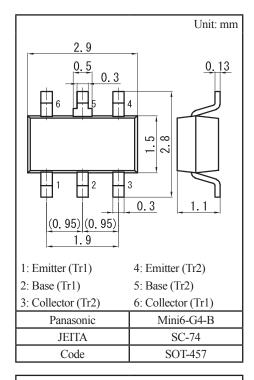
Dual DSC2002 (Individual)

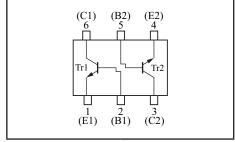
#### Packaging

 $DMC204020R \quad Embossed \ type \ (Thermo-compression \ sealing): \ 3\ 000\ pcs\ /\ reel \ (standard)$ 

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

|            | Parameter                             | Symbol           | Rating      | Unit |
|------------|---------------------------------------|------------------|-------------|------|
| Tr1<br>Tr2 | Collector-base voltage (Emitter open) | V <sub>CBO</sub> | 60          | V    |
|            | Collector-emitter voltage (Base open) | V <sub>CEO</sub> | 50          | V    |
|            | Emitter-base voltage (Collector open) | $V_{\rm EBO}$    | 5           | V    |
|            | Collector current                     | $I_{C}$          | 500         | mA   |
|            | Peak collector current                | $I_{CP}$         | 1           | A    |
| Overall    | Total power dissipation               | P <sub>T</sub>   | 300         | mW   |
|            | Junction temperature                  | T <sub>j</sub>   | 150         | °C   |
|            | Operating ambient temperature         | T <sub>opr</sub> | -40 to +85  | °C   |
|            | Storage temperature                   | T <sub>stg</sub> | -55 to +150 | °C   |



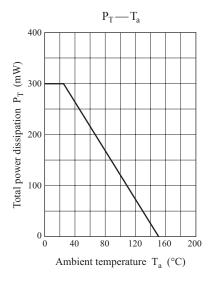


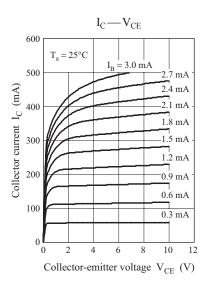
### ■ Electrical Characteristics $T_a = 25$ °C±3°C

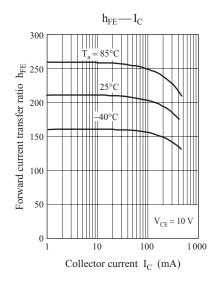
| Parameter  | Symbol               | Conditions  | Min | Тур | Max | Unit |
|--|----------------------|---|-----|-----|-----|------|
| Collector-base voltage (Emitter open)                            | $V_{CBO}$            | $I_C = 10 \mu A, I_E = 0$                           | 60  |     |     | V    |
| Collector-emitter voltage (Base open)                            | V <sub>CEO</sub>     | $I_C = 2 \text{ mA}, I_B = 0$                       | 50  |     |     | V    |
| Emitter-base voltage (Collector open)                            | $V_{EBO}$            | $I_E = 10 \mu A, I_C = 0$                           | 5   |     |     | V    |
| Collector-base cutoff current (Emitter open)                     | $I_{CBO}$            | $V_{CB} = 20 \text{ V}, I_E = 0$                    |     |     | 0.1 | μА   |
| F 1 0 *1   | h <sub>FE1</sub>     | $V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$     | 120 |     | 340 | _    |
| Forward current transfer ratio *1                                | h <sub>FE2</sub>     | $V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$     | 40  |     |     |      |
| Collector-emitter saturation voltage                             | V <sub>CE(sat)</sub> | $I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$         |     | 0.1 | 0.6 | V    |
| Transition frequency   | $f_T$                | $V_{CE} = 10 \text{ V}, I_{C} = 50 \text{ mA}$      |     | 160 |     | MHz  |
| Collector output capacitance (Common base, input open circuited) | C <sub>ob</sub>      | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ |     | 4.8 | 15  | pF   |

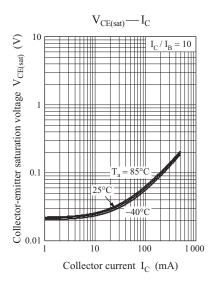
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

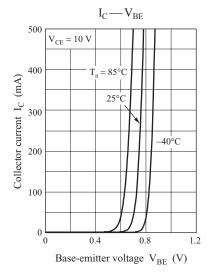
2. \*1: Pulse measurement

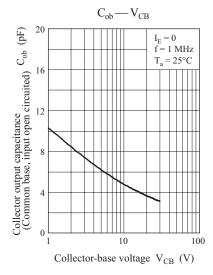


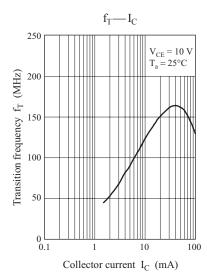








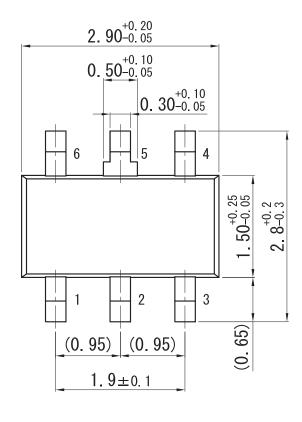


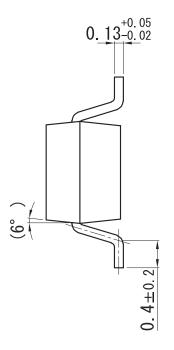


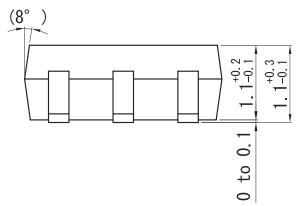
Ver. DED 2

Mini6-G4-B

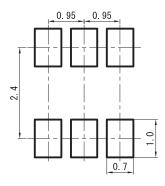
Unit: mm







### ■ Land Pattern (Reference) (Unit: mm)



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